#### TOSHIBA Schottky Barrier Diode

# CLS03

Switching-Mode Power Supply (Secondary-Rectification) Applications (Low Voltage)

DC/DC Converter Applications

• Forward voltage:  $V_{FM} = 0.58 \text{ V (max)}$ 

• Average forward current: IF (AV) = 10 A

• Repetitive peak reverse voltage: VRRM = 60 V

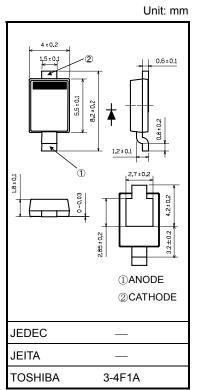
• Suitable for compact assembly due to small surface-mount package: "L-FLAT<sup>TM</sup>" (Toshiba package name)

## **Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Repetitive peak reverse voltage	$V_{RRM}$	60	V
Average forward current	I <sub>F (AV)</sub>	10 (Note)	Α
Non-repetitive peak surge current	I <sub>FSM</sub>	100 (50 Hz)	Α
Junction temperature	Tj	-40~125	°C
Storage temperature range	T <sub>stg</sub>	-40~150	°C

Note:  $T\ell = 70^{\circ}C$ 

Rectangular waveform ( $\alpha$  = 180°),  $V_R$  = 30 V



Weight: 0.15 g (typ.)

# **Electrical Characteristics (Ta = 25°C)**

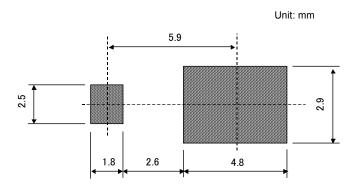
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Peak forward voltage	V <sub>FM (1)</sub>	I <sub>FM</sub> = 3.0 A (pulse test)	_	0.36	_		
	V <sub>FM (2)</sub>	I <sub>FM</sub> = 5.0 A (pulse test)	_	0.41	_	V	
	V <sub>FM (3)</sub>	I <sub>FM</sub> = 10 A (pulse test)	_	0.53	0.58		
Peak repetitive reverse current	I <sub>RRM (1)</sub>	V <sub>RRM</sub> = 5 V (pulse test)	-	7.0		μΑ	
T eak repetitive reverse current	I <sub>RRM (2)</sub>	V <sub>RRM</sub> = 60 V (pulse test)		0.1	1.0	mA	
Junction capacitance	Cj	V <sub>R</sub> = 10 V, f = 1.0 MHz	_	345	_	pF	
Thermal resistance (junction to ambient)	R <sub>th (j-a)</sub>	Device mounted on a glass-epoxy board (board size: 50 mm × 50 mm) (board thickness: 1.6 t) (soldering land) Cathode 5.7 mm × 6.2 mm Anode 4.5 mm × 3.4 mm			100	°C/W	
Thermal resistance (junction to lead)	R <sub>th (j-l)</sub>	_	_	_	5	°C/W	

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#### Marking

Abbreviation Code	Part No.		
S03	CLS03		

#### **Standard Soldering Pad**

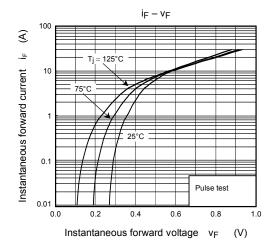


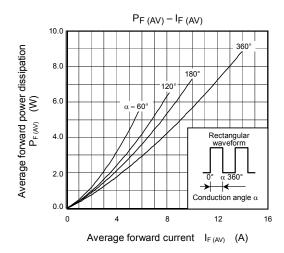
# **Handling Precautions**

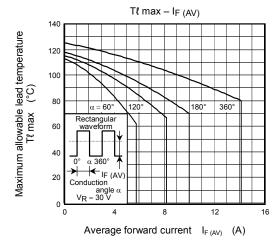
- 1) Schottky barrier diodes have reverse current characteristics compared to other diodes. There is a possibility that SBD will cause thermal runaway when used under high-temperature or high-voltage conditions. Be sure to take forward and reverse loss into consideration during design.
- 2) The maximum ratings denote the absolute maximum ratings, which are rated values that must not be exceeded during operation, even for an instant. The following are the general derating methods that we recommend for when designing a circuit incorporating this device.
  - $V_{RRM}$ : Use this rating with reference to (1) above.  $V_{RRM}$  has a temperature coefficient of 0.1%/°C. Take this temperature coefficient into account when designing a device for operation at low temperature.
  - IF (AV): We recommend that the worst case current be no greater than 80% of the maximum rating of IF (AV) and that  $T_j$  be below 100°C. When using this device, take the margin into consideration by using an allowable Tamax-IF (AV) curve.
  - IFSM: This rating specifies the non-repetitive peak current. This applies only to abnormal operation, which seldom occurs during the lifespan of the device.
  - $T_j$ : Derate this rating when using the device in order to ensure high reliability. We recommend that the device be used at a  $T_j$  of below 100°C.
- 3) Thermal resistance between junction and ambient fluctuates depending on the mounting condition condition of the device. When using the device, design the circuit board and soldering land size to match the appropriate thermal resistance value.

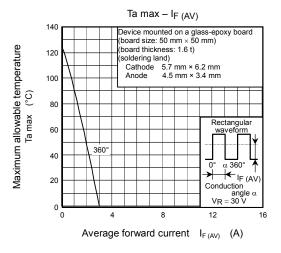
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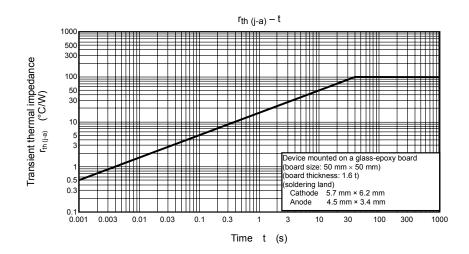
4) Refer to the databook on Rectifiers for further information.



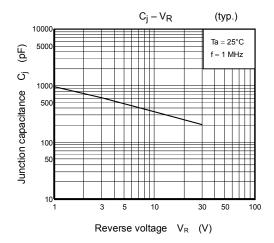


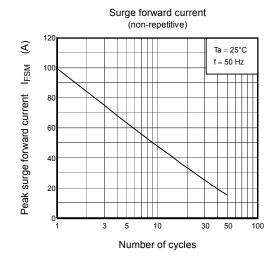


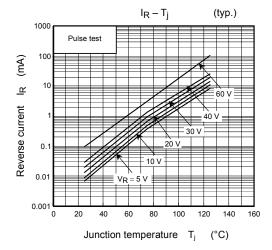


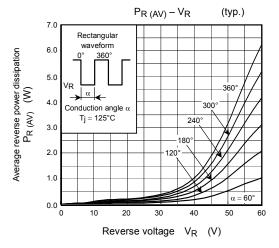


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Handbook" etc..

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